

FEB 27 2006

Atty. Dkt. No. 039153-0649 (H0982)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**Applicant:** Xiang et al.**Title:** FULLY DEPLETED STRAINED SILICON ON INSULATOR TRANSISTOR AND METHOD OF MAKING THE SAME**Appl. No.:** 10/773,026**Filing Date:** 02/05/2004**Examiner:** Doty, Heather Anne**Art Unit:** 2813

CERTIFICATE OF FACSIMILE TRANSMISSION
 I hereby certify that this paper is being facsimile transmitted to the United States Patent and Trademark Office, Alexandria, Virginia on the date below.

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AMENDMENT AND REPLY UNDER 37 CFR 1.111

Mail Stop AMENDMENT
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, VA 22313-1450

Sir:

This communication is responsive to the Non-Final Office Action dated November 30, 2005, concerning the above-referenced patent application.

Amendment to the Title begin on page 3 of this document.

Amendments to the Abstract are presented as a new Abstract attached to this document for insertion after the claim pages of the application (or to replace the previously submitted Abstract).

Amendments to the Claims are reflected in the listing of claims which begins on page 4 of this document.

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Remarks/Arguments begin on page 8 of this document.

Please amend the application as follows:

MILW_1930479.1

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Application No. 10/773,026

Atty. Dkt. No. 039153-0649 (H0982)

Amendments to the Title:

Please amend the Title as follows;

**FULLY DEPLETED STRAINED SILICON SEMICONDUCTOR ON INSULATOR
TRANSISTOR AND METHOD OF MAKING THE SAME**

MILW_1930479.1

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Application No. 10/773,026